

PRELIMINARY AMENDMENT

New U.S. National Stage Application to Hiroto OHTAKE, et al.

AMENDMENTS TO THE SPECIFICATION

Please amend the first paragraph on page 51 as shown below:

On the other hand, in the third embodiment, following the formation of the modified layer 26a onto the sidewall of the organic interlayer film 26, the formations of the barrier film 30 and the copper film 31 are carried out. Thus, in the third embodiment, the damage given to the modified layer 26a is little. The fact that the damage of the modified layer 26a is little is preferable in that the effect of ~~diffusing the copper~~ prevention of diffusion of the copper from the copper film 31 becomes high.

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Please delete the present Abstract of the Disclosure and replace it with the following new Abstract of the Disclosure.

A technique is provided for protecting an interlayer insulating film formed of an organic low dielectric constant material from any damage applied in a semiconductor process, and for attaining the decrease leak current in the interlayer insulating film, resulting in the improvement of reliability of a semiconductor device. The semiconductor device according to the present invention has an organic insulating films (~~5, 26, 28~~) having openings. The organic insulating films (~~5, 26, 28~~) have modified portions (~~5a, 26a, 28a~~) facing the openings. The modified portions (~~5a, 26a, 28a~~) contains fluorine atoms and nitrogen atoms. The concentration of the fluorine atoms in the modified portions (~~5a, 26a, 28a~~) is lower than the concentration of the nitrogen atoms. The above-mentioned modified layers (~~5a, 26a, 28a~~) protect the semiconductor device from the damage applied in the semiconductor process, while suppressing the corrosion of the conductors embedded in the openings.